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Ruby

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(54) **CAPACITANCE DETECTOR FOR ACCELEROMETER AND GYROSCOPE AND ACCELEROMETER AND GYROSCOPE WITH CAPACITANCE DETECTOR**

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CPC **G01P 15/125** (2013.01); **G01P 15/0802** (2013.01); **G01P 2015/0831** (2013.01); **G01C 19/5776** (2013.01)

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See application file for complete search history.

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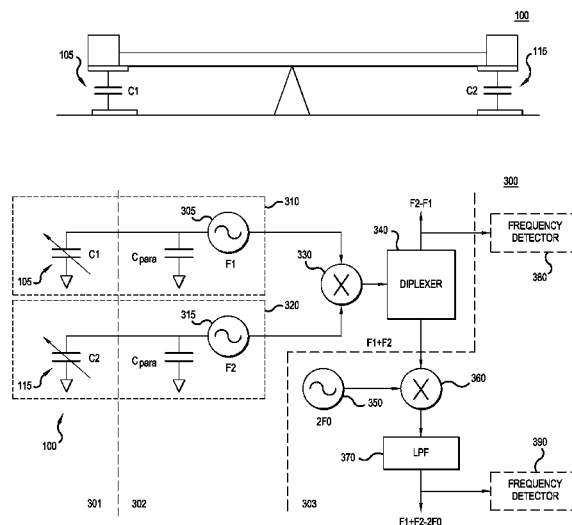
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(57) **ABSTRACT**

A capacitance-to-frequency converter is configured to convert a difference between first and second capacitances produced of a teeter-totter capacitive transducer as a result of a rotational force being applied to the teeter-totter capacitive transducer to a first signal having a first frequency that is a function of the rotational force, and to convert a sum of the first and second capacitances produced as a result of an acceleration force to a second signal having a second frequency that is a function of the acceleration force. The capacitance-to-frequency converter includes a first oscillator having a first oscillator frequency that changes in response to a change in the first capacitance; a second oscillator having a second oscillator frequency that changes in response to a change in the second capacitance; and a mixer having first and second mixer inputs connected outputs of the first and second oscillators.

18 Claims, 8 Drawing Sheets



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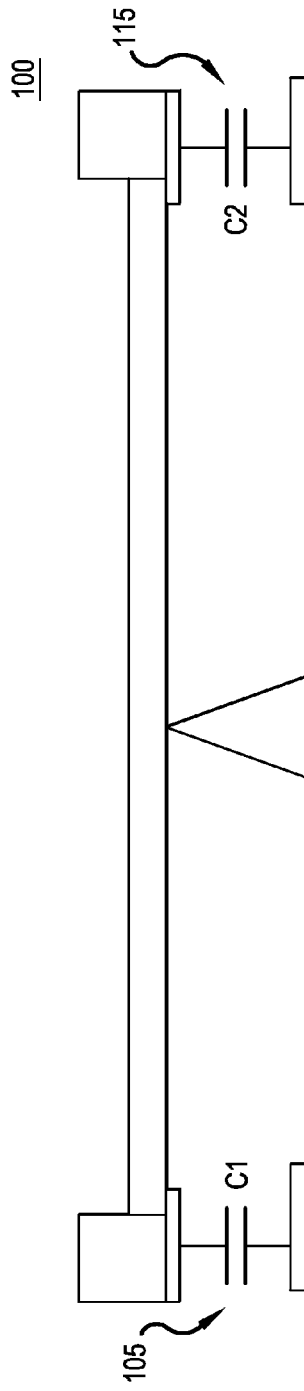


FIG. 1A

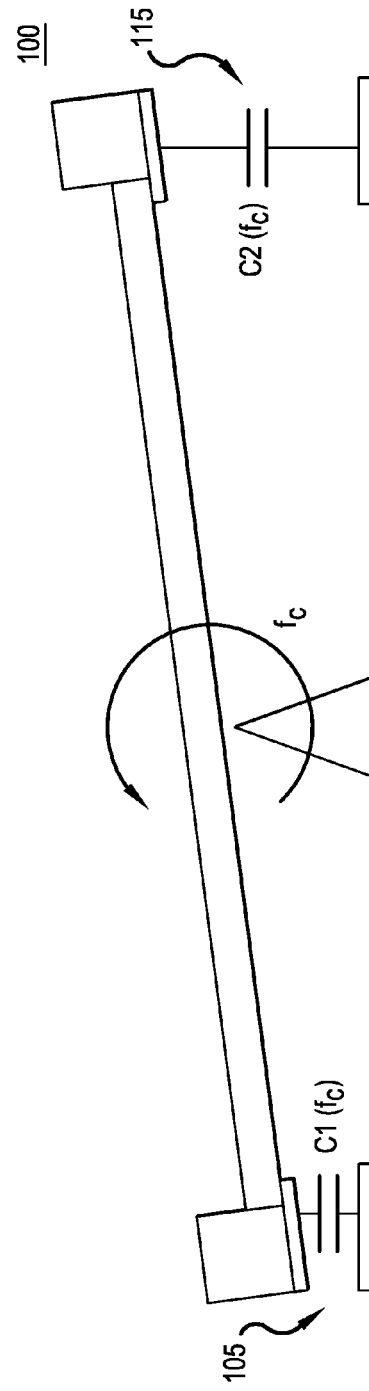


FIG. 1B

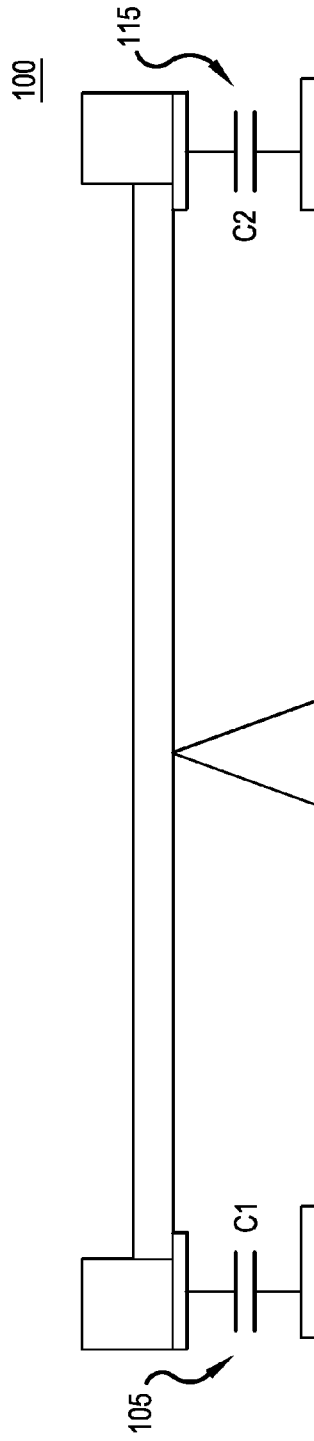


FIG. 1C

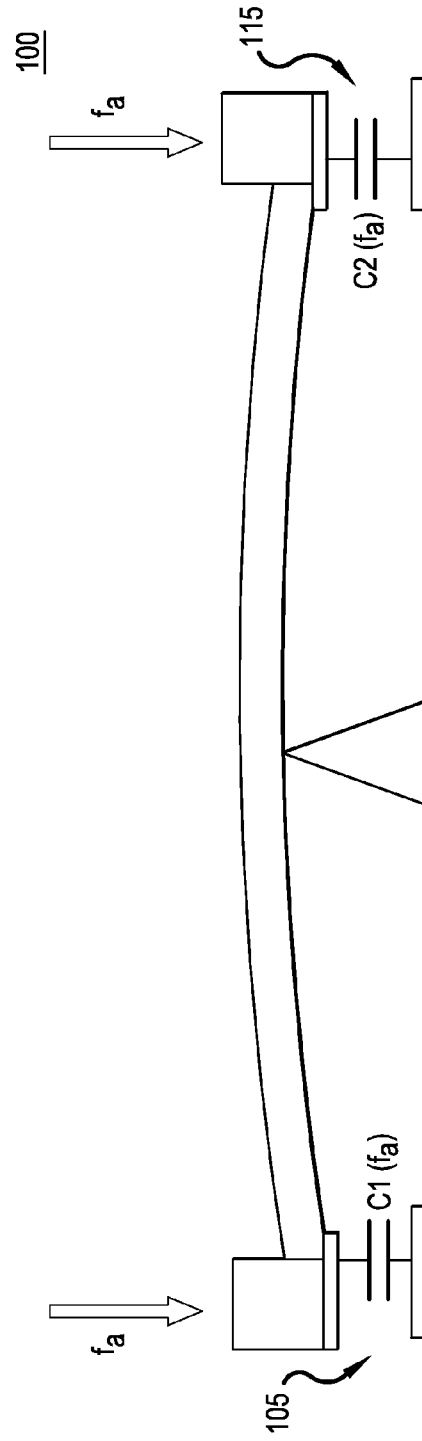


FIG. 1D

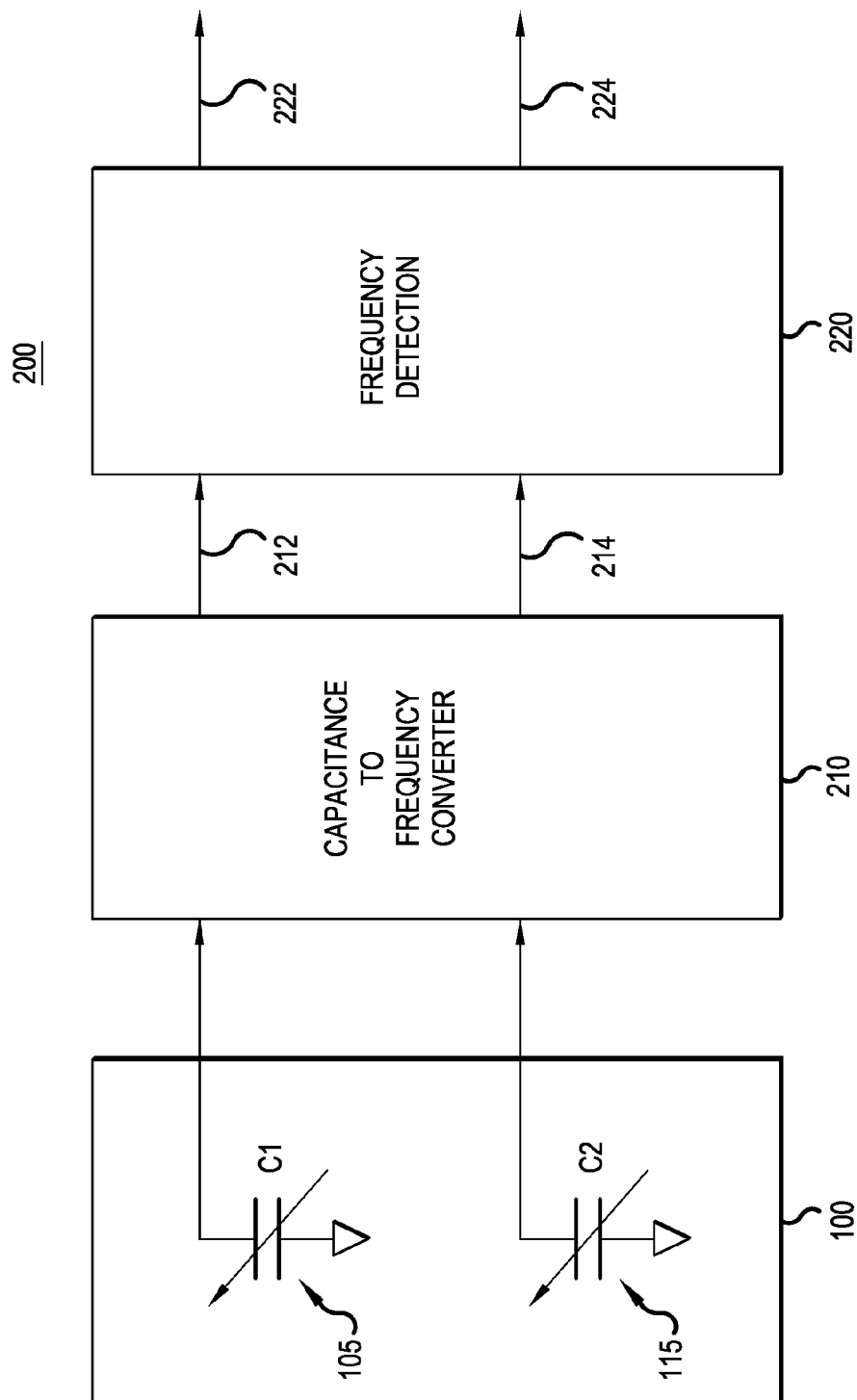


FIG.2

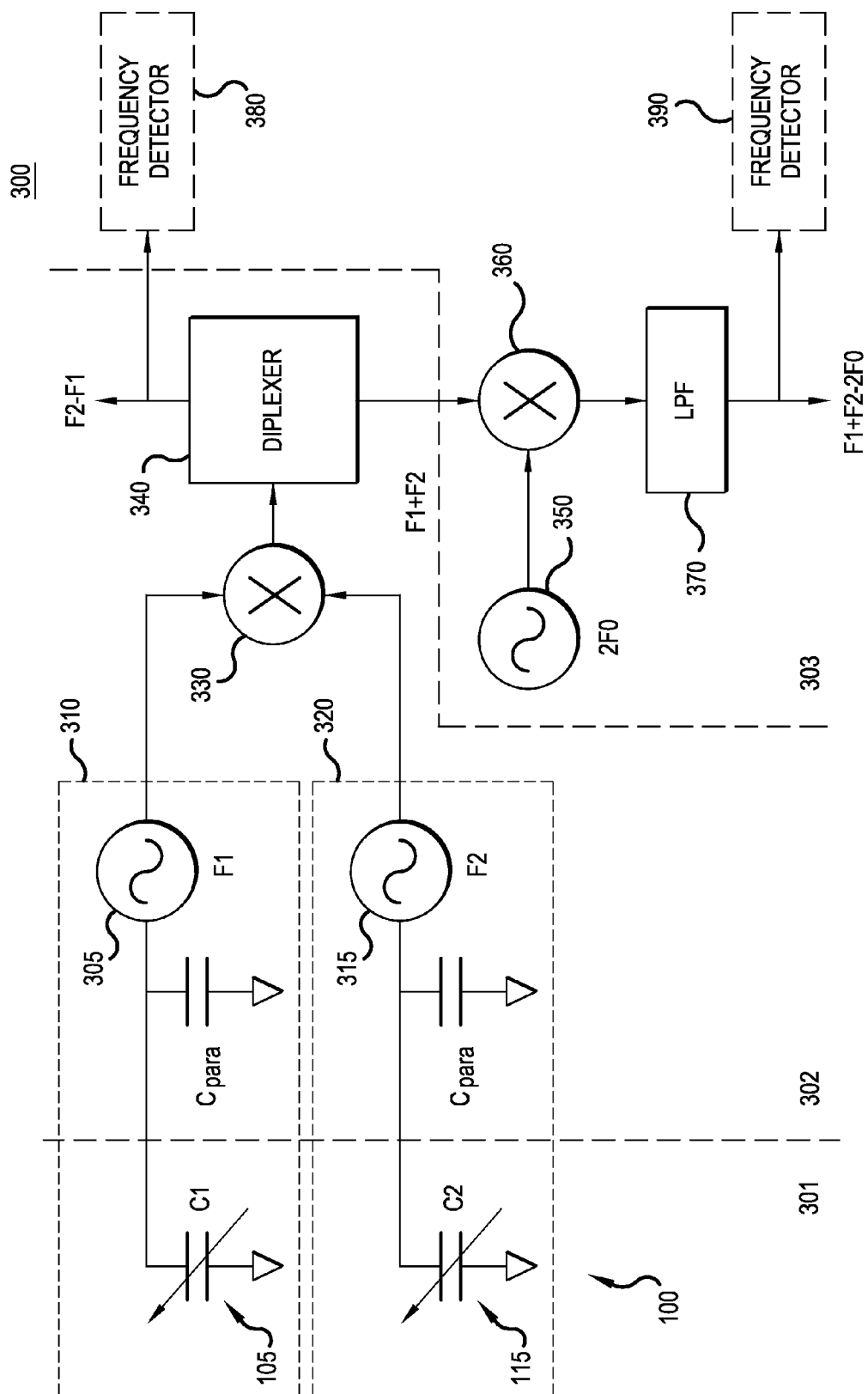


FIG.3

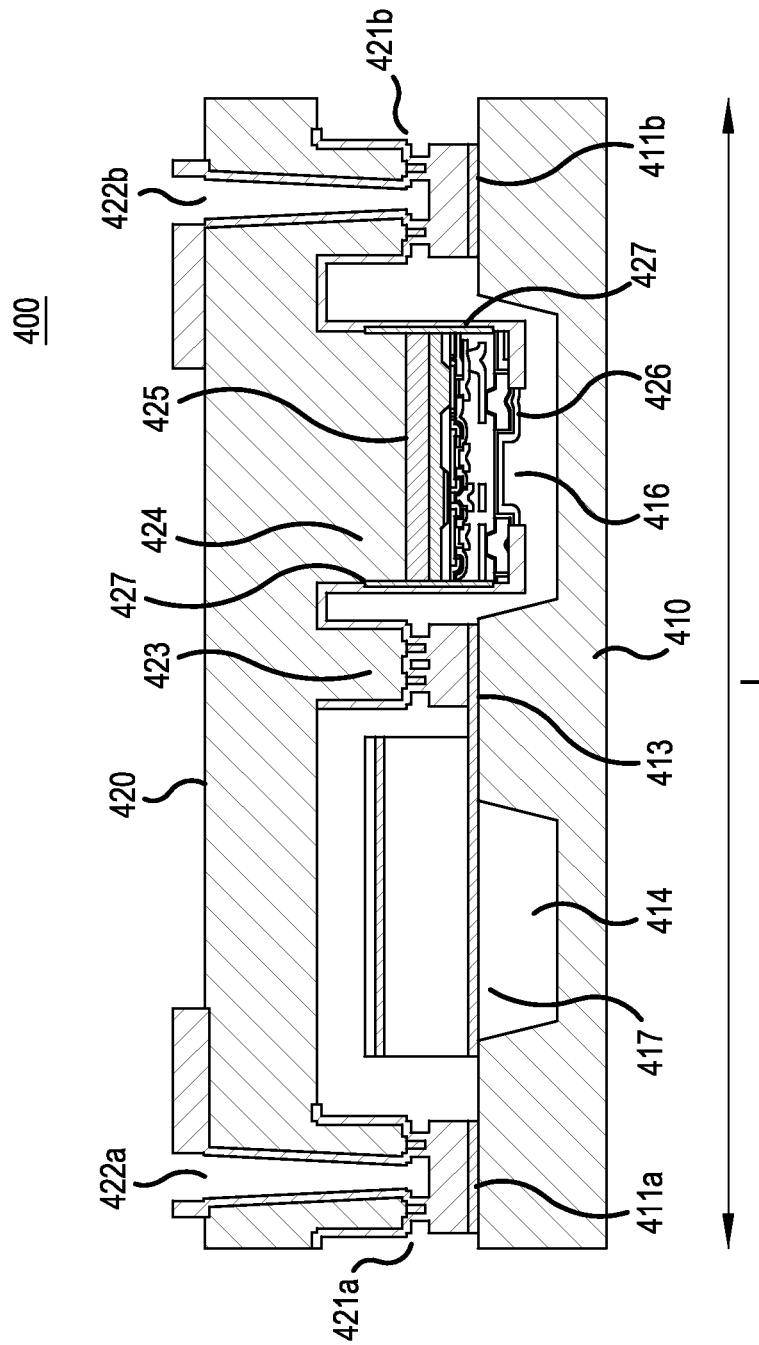


FIG.4

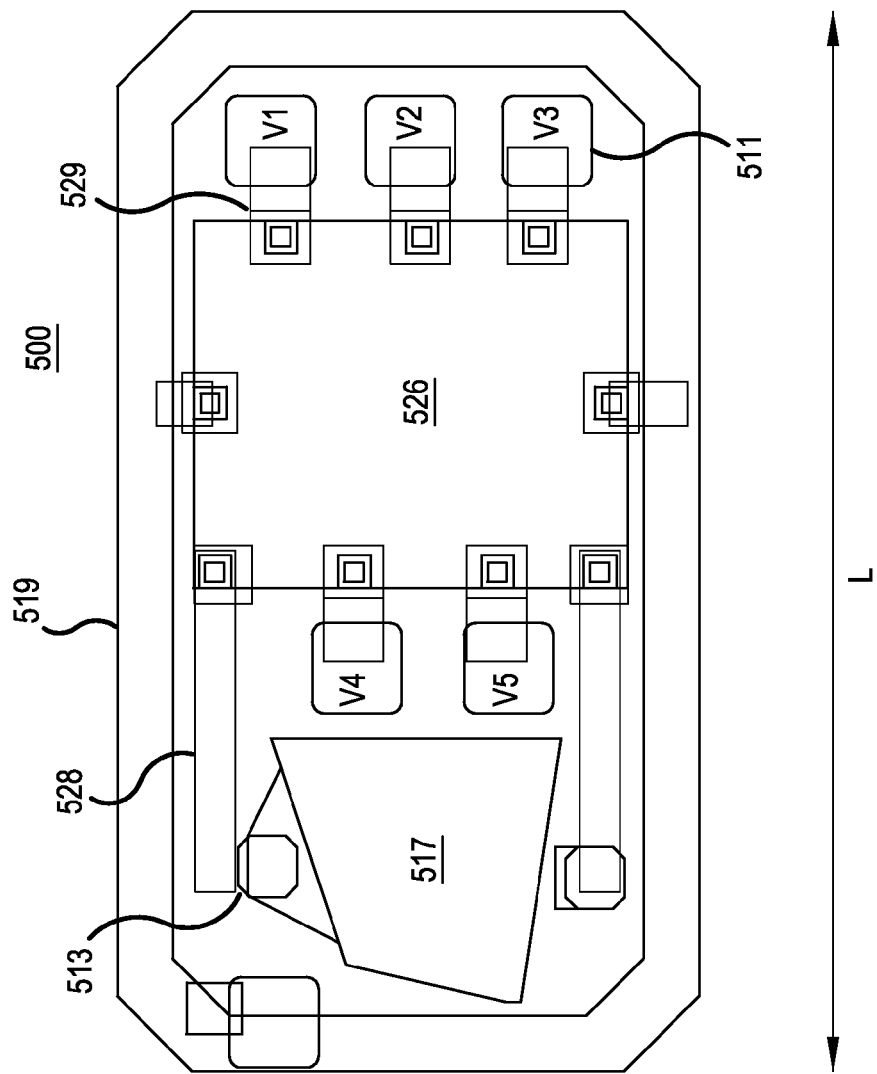


FIG.5

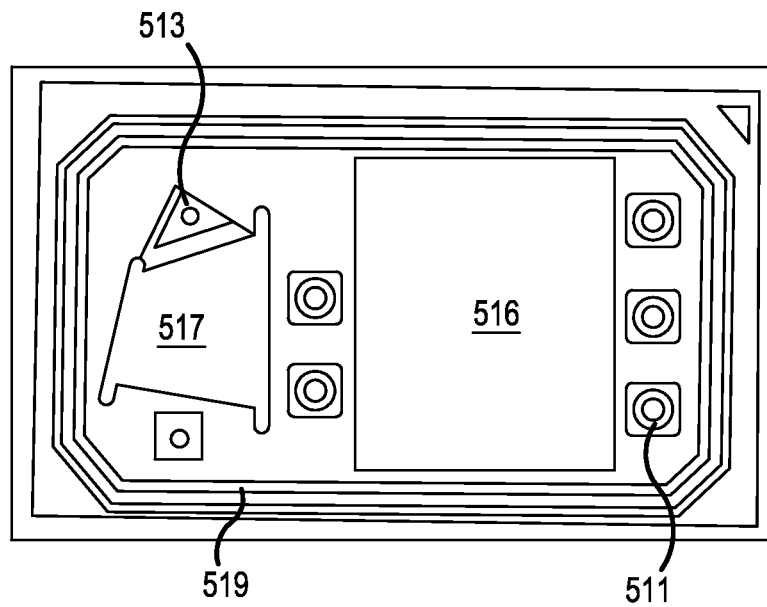


FIG. 6A

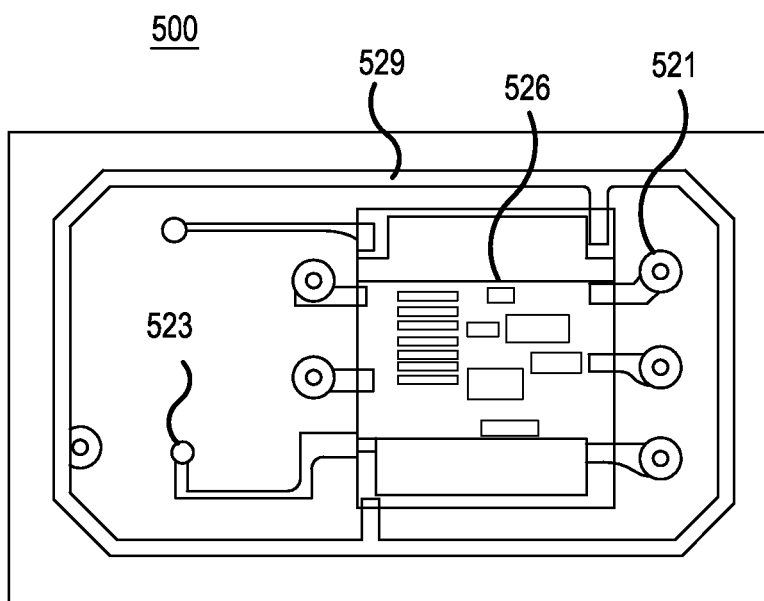


FIG. 6B

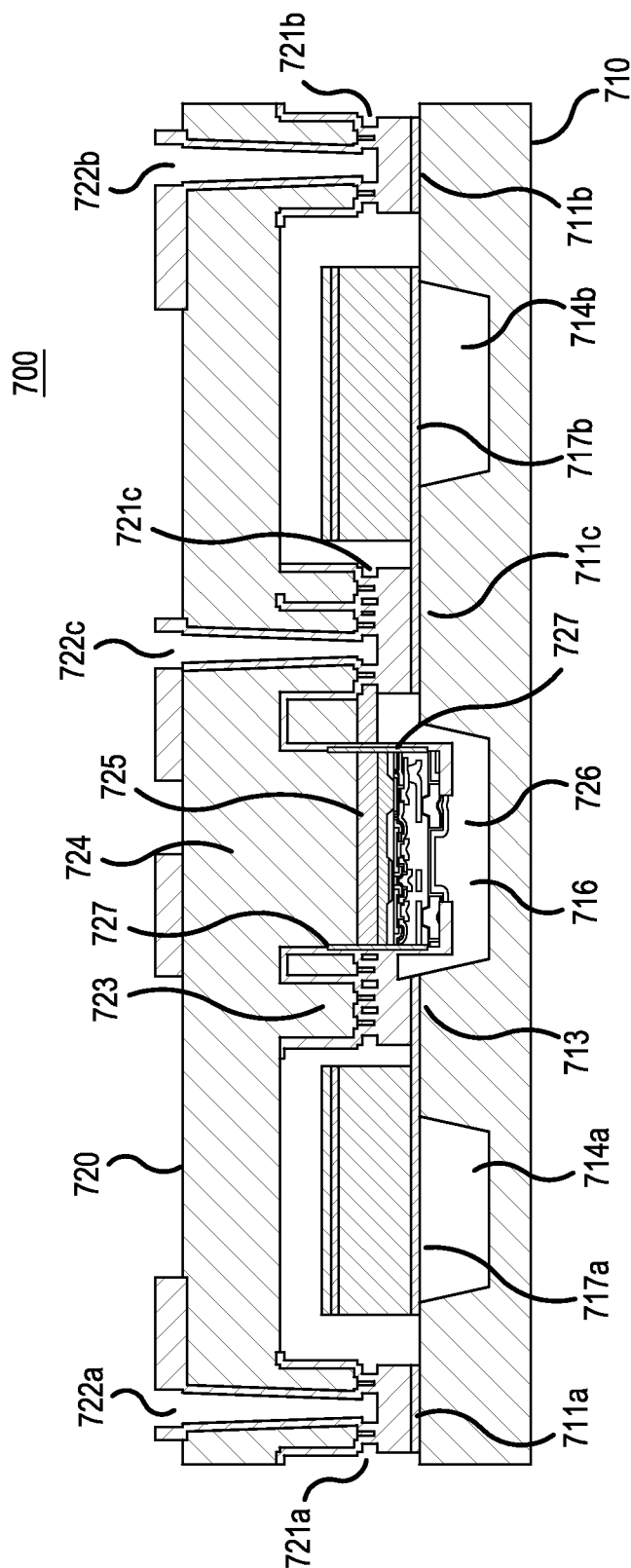


FIG. 7

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CAPACITANCE DETECTOR FOR ACCELEROMETER AND GYROSCOPE AND ACCELEROMETER AND GYROSCOPE WITH CAPACITANCE DETECTOR

BACKGROUND

There are an increasing number of devices where it is desired or needed to be able to detect and quantify an acceleration (i.e., a linear acceleration) force and/or a rotational force that is applied to the device. In particular, many game-playing devices and portable electronic devices need to be able to detect rotation and movement of the device. For example, a number of devices use accelerometers to orient the display of an image on a display screen to match the orientation in which the device is held, i.e., switching between portrait and landscape modes depending upon how the device is held. Such devices include some tablet personal computers (PCs), smart phones, and digital cameras

Currently, microelectromechanical system (MEMS) accelerometers and gyroscopes are generally used in these devices for detecting and quantifying acceleration (linear motion) and rotational motion. For example, the current version of the SONY WII MOTIONPLUS® expansion device for the WII® Remote video game controller for the WII® home video game system uses a dual-axis tuning fork gyroscope and a single-axis gyroscope which can determine rotational motion.

Gyroscopes are also useful for “dead reckoning” of a device. That is, a gyroscope can be used to track a device’s movements and turns, for example to show the device’s location on a map—which may be particularly useful when the device is inside a building or underground or otherwise isolated from Global Positioning System (GPS) signals.

It would be desirable, therefore, to provide a device that can measure both acceleration and rotation. It would also be desirable to provide a method of detecting both acceleration and rotation.

BRIEF DESCRIPTION OF THE DRAWINGS

The example embodiments are best understood from the following detailed description when read with the accompanying drawing figures. It is emphasized that the various features are not necessarily drawn to scale. In fact, the dimensions shown in the drawings may be arbitrarily increased or decreased for clarity of discussion. Wherever applicable and practical, like reference numerals refer to like elements.

FIGS. 1A-B illustrate principles of operation of a microelectromechanical system (MEMS) teeter-totter capacitive transducer for detecting rotation (from the Coriolis Force, f_c).

FIGS. 1C-D illustrate principles of operation of a MEMS teeter-totter capacitive transducer for detecting acceleration (fa).

FIG. 2 is a high level functional block diagram of one example embodiment of a device that may function as a combined accelerometer and rotation detector.

FIG. 3 is a more detailed functional block diagram of one example embodiment of a device that may function as a combined accelerometer and rotation detector.

FIG. 4 shows a cross-sectional view of a portion of one example embodiment of a packaged FMOS device.

FIG. 5 shows a top cutaway view of another example embodiment of a packaged FMOS device.

FIGS. 6A-B show two substrates employed in the packaged FMOS device of FIG. 5.

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FIG. 7 shows an example embodiment of a packaged FMOS device with two FBAR resonators that may be employed in a combined accelerometer and rotation detector.

DETAILED DESCRIPTION

In the following detailed description, for purposes of explanation and not limitation, example embodiments disclosing specific details are set forth in order to provide a thorough understanding of an embodiment according to the present teachings. However, it will be apparent to one having ordinary skill in the art having had the benefit of the present disclosure that other embodiments according to the present teachings that depart from the specific details disclosed herein remain within the scope of the appended claims. Moreover, descriptions of well-known apparatus and methods may be omitted so as to not obscure the description of the example embodiments. Such methods and apparatus are clearly within the scope of the present teachings.

Unless otherwise noted, when a first device is said to be connected to a second device, this encompasses cases where one or more intermediate devices may be employed to connect the two devices to each other. However, when a first device is said to be directly connected to a second device, this encompasses only cases where the two devices are connected to each other without any intermediate or intervening devices. Similarly, when a signal is said to be coupled to a device, this encompasses cases where one or more intermediate devices may be employed to couple the signal to the device. However, when a signal is said to be directly coupled to a device, this encompasses only cases where the signal is directly coupled to the device without any intermediate or intervening devices. As used herein, “approximately” means within 10% and “substantially” means within 5%. As used herein, when a first structure, material, or layer is the to cover a second structure, material, or layer, this includes cases where the first structure, material, or layer substantially or completely encases or surrounds the second structure, material or layer.

FIGS. 1A-B illustrate principles of operation of a microelectromechanical system (MEMS) teeter-totter capacitive transducer **100** for detecting rotation which can be employed in a rotation detector or gyroscope. First and second capacitors **105** and **115** are provided at opposite ends of MEMS teeter-totter capacitive transducer **100**.

FIG. 1A illustrates the MEMS proof mass at rest, in the absence of a rotational force being applied to MEMS teeter-totter capacitive transducer **100**. In a typical arrangement, when the MEMS proof mass is at rest as shown in FIG. 1A, and no rotational or acceleration force is applied to it, the capacitance C1 of capacitor **105** is substantially the same as the capacitance C2 of capacitor **115**:

$$C1 \approx C2 + \sigma, \quad (1)$$

where $C1 \approx C2 \gg \sigma$, and σ may reflect the effect of manufacturing tolerances for MEMS teeter-totter capacitive transducer **100**. In some embodiments, σ may be less than 5 percent of C1 or C2. In some embodiments, σ may be less than 2 percent of C1 or C2.

FIG. 1B illustrates the MEMS proof mass when a Coriolis (rotational) force, f_c , is applied to MEMS teeter-totter capacitive transducer **100**. As shown in FIG. 1B, when the rotational force is applied to the MEMS proof mass, the capacitances of first and second capacitors **105** and **115** change as a result of the rotational force. Indeed, the changes in the capacitances, $\Delta C1$ and $\Delta C2$, are functions of the rotational force, f_c : $\Delta C1(f_c)$ and $\Delta C2(f_c)$, where:

$$\Delta C1(f_c) \approx -\Delta C2(f_c) = \Delta C_{1,2}(f_c) \quad (2)$$

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In the example shown in FIG. 1B, when a counterclockwise rotational force is applied to MEMS teeter-totter capacitive transducer 100, the capacitance of capacitor 105 increases, and the capacitance of capacitor 115 decreases. The opposite happens in response to a clockwise rotational force.

To detect a change in capacitance, an AC signal may be applied to one or both capacitors such that a change in the capacitance produces a change in the impedance the capacitor presents to the AC signal. A low noise amplifier may convert the change in impedance presented by the capacitor to the AC signal to a voltage that is a function of the rotational force.

FIGS. 1C-D illustrate principles of operation of a MEMS teeter-totter capacitive transducer 100 for detecting acceleration.

FIG. 1C like FIG. 1A illustrates the proof mass at rest when no acceleration force is applied to it, and again the capacitance C1 of capacitor 105 is substantially the same as the capacitance C2 of capacitor 115.

FIG. 1D illustrates the MEMS proof mass when an acceleration (i.e., a linear acceleration) force is applied to MEMS teeter-totter capacitive transducer 100. As shown in FIG. 1D, when the acceleration force is applied, the capacitances of first and second capacitors 105 and 115 change as a result of the acceleration force. Indeed, the change in the capacitances, $\Delta C1$ and $\Delta C2$, are functions of the acceleration force, f_A : $\Delta C1(f_A)$ and $\Delta C2(f_A)$, where:

$$\Delta C1(f_A) \approx \Delta C2(f_A) \approx \Delta C_{1,2}(f_A) \quad (3)$$

In the example shown in FIG. 1D, when a downward acceleration force is applied to MEMS teeter-totter capacitive transducer 100, the capacitances of both capacitors 105 and 115 increase from their nominal values C1 and C2. The opposite happens in response to an upward acceleration force.

Accordingly, net positive (or negative) changes in charges on first and second capacitors 105 and 115 can be linked to an acceleration force being applied to MEMS teeter-totter capacitive transducer 100.

FIG. 2 is a high level functional block diagram of one example embodiment of a device 200 that may function as a combined accelerometer and rotation detector.

Device 200 includes MEMS teeter-totter capacitive transducer 100, a capacitance-to-frequency converter 210, and frequency detection block 220.

Capacitance-to-frequency converter 210 is configured to convert a change in the first and second capacitances of first and second capacitors 105 and 115 produced as a result of a rotational force being applied to teeter-totter capacitive transducer 100 to a change in the first frequency of a first signal 212. Capacitance-to-frequency converter 210 is also configured to convert a change in the first and second capacitances of first and second capacitors 105 and 115 produced as a result of an acceleration force (i.e., a linear acceleration force) being applied to teeter-totter capacitive transducer 100 to a change in a second frequency of a second signal 214.

Frequency detection block 220 detects the first and second frequencies of first and second signals 212 and 214 and outputs: a rotational force detection signal 222 that indicates the rotational force that is applied to MEMS teeter-totter capacitive transducer 100; and an acceleration force detection signal 224 that indicates the acceleration force that is applied to MEMS teeter-totter capacitive transducer 100. In some embodiments, frequency detection block 220 may include frequency counters for each of the first and second signals 212 and 214, or may include some other type of frequency detector, such as a discriminator, a phase-lock loop (PLL) frequency detector, etc.

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Device 200 can detect both acceleration (i.e., linear acceleration), and rotation in one plane. For a three dimensional gyroscope, three devices 200 can be employed for detecting first, second, and third rotational forces in three different corresponding planes (e.g., orthogonal planes) that span three dimensional space.

FIG. 3 is a more detailed functional block diagram of one embodiment of a device 300 that may function as a combined accelerometer and rotation detector. In particular, device 300 may be one embodiment of the device 200 shown in FIG. 2.

Device 300 comprises: first and second oscillators 310 and 320; a first mixer 330; a diplexer 340; a third oscillator 350; a second mixer 360; a filter (e.g., a low pass filter (LPF)) 370; and optionally first and second frequency detectors 380 and 390 (in some embodiments, frequency detection may be performed externally to device 300).

First oscillator 310 operates at a first oscillator frequency, and second oscillator 320 operates at a second oscillator frequency. First and second oscillators 310 and 320 include first and second oscillator circuits 305 and 315, respectively, and further include first and second capacitors 105 and 115, respectively, of MEMS teeter-totter capacitive transducer 100. More specifically, first and second capacitors 105 and 115 form part of the resonant circuits of the first and second oscillators 310 and 320, respectively. Therefore, the first and second frequencies of first and second oscillators 310 and 320 change in response to changes in the capacitance of capacitor 105 and the capacitance of capacitor 115, respectively, for example in response to a rotational force and/or an acceleration force applied to MEMS teeter-totter capacitive transducer 100. Accordingly, the first and second oscillator frequencies may be expressed as a function of the acceleration force and the rotational force: $F1(f_A, f_C)$ and $F2(f_A, f_C)$, respectively.

In the absence of any rotational force (f_C) or acceleration force (f_A) being applied to MEMS teeter-totter capacitive transducer 100, first oscillator 310 operates at a nominal first oscillator frequency $F1_{NOM}$, and second oscillator 320 operates at a nominal second oscillator frequency $F2_{NOM}$. In a beneficial embodiment:

$$F2_{NOM} - F1_{NOM} = \delta, \quad (4)$$

where $F1_{NOM} \approx F2_{NOM} = F0 \gg \delta$.

Furthermore:

$$F1_{NOM} = \frac{1}{2\pi\sqrt{L1(C1 + C_{PARA} + C_P)}} \text{ and} \quad (5)$$

$$F2_{NOM} = \frac{1}{2\pi\sqrt{L2(C2 + C_{PARA} + C_P)}} \quad (6)$$

where C_P is the capacitance of the resonator, and C_{PARA} is a parasitic capacitance

If we assume that $C1 \approx C2 = C_{1,2}$, and define:

$$CT = C_{1,2} + C_P + C_{PARA} \quad (7)$$

then, by expanding the square root function, we get:

$$F1(f_A, f_C) \approx F1_{NOM}(1 - 0.5 * (\Delta C_{1,2}(f_C)/C_P) + 0.5 * (\Delta C_{1,2}(f_A)/C_P)) \quad (8)$$

$$F2(f_A, f_C) \approx F2_{NOM}(1 + 0.5 * (\Delta C_{1,2}(f_C)/C_P) + 0.5 * (\Delta C_{1,2}(f_A)/C_P)) \quad (9)$$

In an example embodiment, C_P may be about 0.6 pF, C_{PARA} may be about 0.3 pF, $C_{1,2}$ may be about 0.1 pF, and $\Delta C_{1,2}(f_A)$ and $\Delta C_{1,2}(f_C)$ may each have a maximum range of ± 10 aF (i.e., $\pm 10^{-18}$ F).

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In some embodiments, first and second oscillators **310** and **320** may be temperature stabilized and/or may include a varactor for frequency tuning and/or include a buffer amplifier.

In some embodiments, first and second oscillators **310** and **320** may each include an acoustic resonator, which may be a film bulk acoustic resonator (FBAR), a solidly mounted resonator (SMR), a zero drift resonator (ZDR), or a similar device.

First mixer **330** has first and second mixer inputs connected respectively to outputs of first and second oscillators **310** and **320**, and also has a mixer output that is connected to the input of diplexer **340**.

Diplexer **340** has first and second diplexer outputs which output first and second signals.

The first diplexer output of diplexer **340** provides a first signal that has a first frequency F_X that is the difference between the second oscillator frequency of second oscillator **320**, $F_2(f_A, f_C)$ and the first oscillator frequency of first oscillator **310**, $F_1(f_A, f_C)$. From equations (4), (7) and (8) above we get:

$$F_X = \delta - 0.5 * ((F_2(\Delta C_{1,2}(f_C)/C_Y) + (F_1(\Delta C_{1,2}(f_C)/C_Y)) - \delta - F_0 * \Delta C_{1,2}(f_C)/C_Y) \quad (9)$$

It is seen from equation (9) that the first frequency F_X of the first signal output by diplexer **340** is a function of the rotational force f_C applied to MEMS teeter-totter capacitive transducer **100**. So it is apparent that the rotational force f_C can be ascertained from the first frequency F_X which is the difference between the second oscillator frequency and the first oscillator frequency.

The second diplexer output of diplexer **340** provides a second signal that has a second frequency F_Y that is the sum of the second oscillator frequency of second oscillator **320**, $F_2(f_A, f_C)$ and the first oscillator frequency of first oscillator **310**, $F_1(f_A, f_C)$. From equations (4), (7) and (8) above we get:

$$F_Y = 2F_0 + 0.5 * F_0 * ((\Delta C_{1,2}(f_A)/C_Y) + (\Delta C_{1,2}(f_A)/C_Y)) \quad (10)$$

It is seen from equation (10) that the second frequency F_Y of the second signal output by diplexer **340** is a function of the acceleration force f_A applied to MEMS teeter-totter capacitive transducer **100**. So it is apparent that the acceleration force f_A can be ascertained from the second frequency F_Y .

Although the second frequency F_Y of the second signal output by diplexer **340** is a function of the acceleration force f_A , second frequency F_Y also contains a component at twice the nominal frequency of first and second oscillators **310** and **320** (i.e. at $2 * F_0$). This may make it difficult to extract the desired acceleration information directly from the second signal.

Accordingly, device **300** includes third oscillator **350**, second mixer **360**, and filter (e.g., a low pass filter (LPF)) **370**. In a beneficial arrangement, third oscillator **350** operates at a third oscillator frequency $F_3 = 2 * F_0 + \epsilon$, where $F_0 \gg \epsilon$. Second mixer **360** receives the second signal from diplexer **340** and the third oscillator signal from third oscillator **350** and generates a third signal having a third frequency, F_Z , where:

$$F_Z = \epsilon + F_0 * (\Delta C_{1,2}(f_A)/C_Y) \quad (11)$$

Filter **370** filters out a high frequency component from mixer second **360** at $4 * F_0$.

It is seen from equation (11) that the third frequency F_Z of the third signal output by second mixer **360** (via filter **370**) is a function of the acceleration force f_A applied to MEMS teeter-totter capacitive transducer **100**. So it is apparent that the acceleration force f_A can be ascertained from the third frequency F_Z .

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If desired, the first signal with the frequency F_X and the third signal with the frequency F_Z may be applied to frequency detectors **380** and **390** to quantify the rotational force and the (linear) acceleration force applied to device **300**.

As illustrated in FIG. 3, device **300** may be divided into three components: **301**, **302** and **303**. In some embodiments, component **301** may comprise a first "MEMS" die such as was described above with respect to FIGS. 1A-D, component **302** may comprise a first packaged "FMOS" device as will be described below with respect to FIGS. 4-7, and component **303** may comprise a separate electronic component, which may be another packaged FMOS device. In such embodiments, components **301** and **302** may be packaged tightly together to minimize stray or parasitic capacitance for the oscillators. In particular, packaged FMOS device comprising component **302** may be "flip-chipped" onto the MEMS die comprising component **301**. In other embodiments, components **302** and some or all of the elements in component **303** may be combined into one packaged FMOS device. In other embodiments, the division of elements into the components **301**, **302** and **303** may be different than that shown in FIG. 3. For example, in some embodiments, third oscillator **350**, second mixer **360**, and filter **370** may be included in component **302** (e.g., in a same packaged FMOS device as first and second oscillators **310** and **320** and first mixer **330**).

For a three dimensional gyroscope to measure rotation in three dimensions, three components **301** (i.e., three MEMS teeter-totter capacitive transducers **100**) and three components **302** (i.e., three packaged FMOS devices), together with three second mixers **360** and associated filters **370**, and one third oscillator **350** are needed.

In a beneficial arrangement, component **302** may be provided as a packaged FMOS device using methods and devices disclosed in U.S. Pat. No. 8,232,845 in the names of Richard Ruby, et al., the entirety of which is hereby incorporated herein by references as if fully set forth herein, and aspects of which are discussed below with respect to FIGS. 4-7.

FIG. 4 shows a cross-sectional view of a portion of one example embodiment of a packaged FMOS device **400**. Packaged FMOS device **400** comprises a base substrate **410** and a lid substrate **420**.

Base substrate **410** has on a first surface (top surface as shown in FIG. 4) thereof: first bonding pads **411a** and **411b**; a second bonding pad **413**; a first recessed region **414**; and a second recessed region **416**. Base substrate **410** further includes on the first surface thereof a peripheral pad not shown in FIG. 4, but examples of which are illustrated in FIGS. 5 and 6A. Beneficially, first bonding pads **411a** and **411b**, second bonding pad **413**, and the peripheral pad are formed of an electrically conductive (e.g., metal) material. Also, in some embodiments base substrate **410** may include additional first and second bonding pads **411** and **413**.

Lid substrate **420** has on a first surface (bottom surface as shown in FIG. 4) thereof: bonding pad seals **421a** and **421b**, each having a corresponding through hole **422a** and **422b** formed in lid substrate **420**; a drop down contact post **423**; a pedestal **424**; a low-resistivity material layer region **425**; and electronic circuitry **426** formed on low-resistivity material layer region **425**. Lid substrate **420** further includes on the first surface thereof a peripheral pad seal not shown in FIG. 4, but examples of which are illustrated in FIGS. 2 and 3B. Beneficially, bonding pad seals **421a** and **421b** and drop down contact post **423** each have an electrically conductive (e.g., a metal such as gold) layer thereon for making contact with the corresponding bonding pads **411** and **413**. Also, in some embodiments lid substrate **420** may include additional bonding pad seals **421** and/or additional drop down contact posts

423. In some embodiments, one or more of through holes **422** in lid substrate **420** are plated or otherwise filled with a conductive material (e.g. metal) to provide an electrical connection between the metal layer of a corresponding bonding pad seal **421** and a second surface (top surface as shown in FIG. 4) of lid substrate **420**, for example a pad on the second surface of lid substrate **420**. As shown in FIG. 4, in some embodiments, bonding pad seals **421** and/or drop down contact posts **423** include treads or gaskets that are covered with the electrically conductive material.

Packaged FMOS device **400** further comprises an acoustic resonator **417** disposed on base substrate **410** above first recessed region **414**. In some embodiments, acoustic resonator **417** is electrically connected to electronic circuitry **426**, for example by means of second bonding pad **413** and the conductive (e.g., metal) layer on drop down contact post **423**. In some embodiments, acoustic resonator **417** comprises a film bulk acoustic resonator (FBAR). In other embodiments, a solidly mounted resonator (SMR) may be employed. In some embodiments, electronic circuitry **426** includes one or more transistors or other active devices of an oscillator circuit that operates with acoustic resonator **417** to form an oscillator

In some embodiments, base substrate **410** and/or lid substrate **420** comprise a semiconductor substrate. In some embodiments, lid substrate **420** can be made of an electronically non-conductive material or a high-resistivity semiconductor material, such as single crystal silicon. Also, in some embodiments when lid substrate **420** is a semiconductor substrate, low-resistivity material layer region **425** comprises an epitaxial layer formed on the semiconductor substrate. In alternative embodiments, lid substrate **420** may comprise other high-resistivity materials, for example a silicon-on-insulator (SOT) substrate, and low-resistivity material layer region **425** may be formed by controlled doping of the SOT substrate.

In some embodiments, base substrate **410** and lid substrate **420** are made of materials that have the same or approximately the same coefficient of thermal expansion (CTE) as each other to avoid thermal expansion mismatch problems. In some embodiments base substrate **410** and lid substrate **420** are made of the same semiconductor material as each other.

As noted above, in some embodiments lid substrate **420** is a semiconductor substrate. In general, such a semiconductor substrate on which electronic circuitry **426** is to be fabricated will have a low-resistivity material layer disposed on all or substantially all of a surface thereof for the formation of the semiconductor or active devices of electronic circuitry **426**. In particular, such a low-resistivity material layer comprises a material that has a substantially lower resistivity than the high-resistivity semiconductor material of lid substrate **420**. As used herein, "substantially lower resistivity" means about one order of magnitude lower resistivity, or more than one order of magnitude lower resistivity, for example as measured in terms of Ω -cm. For example, in some embodiments, the high-resistivity semiconductor material of lid substrate **420** has a resistivity of more than 1000 Ω -cm, while the low-resistivity material of a low-resistivity material layer has a resistivity of less than 100 Ω -cm, including in some embodiments a resistivity in a range of 10 Ω -cm. Accordingly, if left intact on lid substrate **420**, such a low-resistivity material layer may provide a low impedance path or electrical short between the conductive (e.g., metal) layer(s) of bonding pad seals **421** and/or drop down contact post(s) **423**. This can degrade the performance of packaged FMOS device **400**, and in some cases may render packaged FMOS device **400** inoperable.

Accordingly, in some embodiments one or more portions of the low-resistivity material layer is removed between bonding pad seals **421**, drop down contact posts **423**, and the peripheral pad seal so as to eliminate a current path through the low-resistivity material layer between any of the bonding pad seals **421**, drop down contact posts **423**, and the peripheral pad seal. Furthermore, in some embodiments one or more portions of the low-resistivity material layer are removed so as to eliminate a current path between low-resistivity material layer region **425** and the conductive layer(s) of some or all of the bonding pad seals **421**, and/or drop down contact posts **423**, and/or the peripheral pad seal.

In a particular embodiment of packaged FMOS device **400** shown in FIG. 4, the low-resistivity material layer (e.g., epitaxial layer) is eliminated except for: (1) low-resistivity material layer (e.g., epitaxial layer) region **425**, which is isolated from some or all of the bonding pad seals **421**, and/or drop down contact posts **423**, and/or the peripheral pad seal; and (2) one or more low-resistivity material layer (e.g., epitaxial layer) portions remaining in the treads of one or more of the bonding pad seal(s) **421**, drop down contact post(s) **423**, and the peripheral pad seal. Furthermore, lid substrate **420** of packaged FMOS device **400** includes an electrically insulating material **427** (e.g., an oxide such as silicon oxide) electrically isolating low-resistivity material layer (e.g., epitaxial layer) region **425** from one or more electrically conductive (e.g., metal) layers or traces in contact with bonding pad seal(s) **421** and drop down contact post(s) **423**. In some embodiments, electrically insulating material **427** partially or totally encompasses or surrounds low-resistivity material layer (e.g., epitaxial layer) region **425**.

In some embodiments, lid substrate **420** may have a low-resistivity material layer (e.g., epitaxial layer) formed entirely on the first surface thereof, and the low-resistivity material layer (e.g. epitaxial layer)—except for low-resistivity material layer (e.g., epitaxial layer) region **425** and the low-resistivity material layer (e.g., epitaxial layer) portions remaining in the treads—may be removed after formation of electronic circuitry **426**. In other embodiments, the low-resistivity material layer (e.g., epitaxial layer)—except for low-resistivity material layer (e.g. epitaxial layer) region **425** and the low-resistivity material layer (e.g., epitaxial layer) portions remaining in the treads—may be removed before formation of electronic circuitry **426**.

In other embodiments, the low-resistivity material layer (e.g., epitaxial layer) is only removed in areas surrounding each of the bonding pad seals **421**, and/or drop down contact posts **423**, and/or the peripheral pad seal so as to electrically isolate the bonding pad seals **421**, and/or drop down contact posts **423**, and/or the peripheral pad seal from each other and/or from electronic circuitry **426**.

FIG. 5 shows a top cutaway view of another example embodiment of a packaged FMOS device **500**. Packaged FMOS device **500** comprises a base substrate **510** and a lid substrate **520**, which are better seen in FIGS. 6A and 6B. FIG. 5 illustrates an electrically conductive trace or connection **528** between electronic circuitry **526** and an acoustic resonator **517** of packaged FMOS device **500** via second bonding pad **513** and drop down contact post **523** (see FIG. 6B), and an electrically conductive trace or connection **529** between electronic circuitry **526** of packaged FMOS device **500** and first bonding pad **511** via bonding pad seal **511**. FIG. 5 also shows that acoustic resonator **517** is laterally offset with respect to electronic circuitry **526** in packaged FMOS device **500**.

In particular, FIG. 6A shows base substrate **510**, and FIG. 6B shows lid substrate **520**. FIG. 6A illustrates first bonding pad **511**, second bonding pad **513**, peripheral pad **519**, a

second recessed region **516** that is disposed beneath electronic circuitry **526** when base substrate **510** is bonded to lid substrate **520** to form packaged FMOS device **500**. FIG. **6B** shows peripheral pad seal **529**, bonding pad seal **521**, and drop down contact post **523**.

Packaged FMOS **500** may include features described above with respect to packaged FMOS device **400**, including electrical isolation of an epitaxial layer region on lid substrate **520** from bonding pad seal **521**, drop down contact post **523** and peripheral pad seal **529**.

In some embodiments, base substrates **410/510**, and lid substrates **420/520**, are configured to be parametrically tested individually prior to assembly.

An example process of assembling packaged FMOS devices **400** and **500** will now be described.

In the example embodiment, bonding pad treads or gaskets of bonding pad seal(s) match the perimeters of the first bonding pad(s) on the base substrate, drop down contact post treads or gaskets of drop down contact post(s) match the perimeters of the second bonding pad(s) on the base substrate, and peripheral pad treads or gaskets of the peripheral pad seal match the peripheral pad on the base substrate. Wells are located inside the perimeters of the bond pad gaskets and are formed to a predetermined depth in the lid substrate. The lid substrate is then placed over the base substrate so as to bond (e.g., a cold weld bond) the peripheral pad seal to the peripheral pad, and to like wise bond the bonding pad seal(s) and the drop down contact post(s) to corresponding bonding pad(s) and form a hermetically sealed volume between the bonding pad seals and the peripheral pad seal. The lid substrate is thinned to form a "microcap." Essentially, the microcap is thinned below a predetermined depth until the wells become through holes that provide access for making an electrical connection to the bonding pads inside the package, but outside the hermetically sealed volume, for external conductors, which may include conductive wires provided inside the through holes and/or a conductive (e.g. metal) layer plated or deposited in the through holes. This arrangement assures a highly reliable hermetic seal for devices (e.g., electronic circuitry and acoustic resonator) inside the package, while allowing electrical connections without passing through a seal. Further, this process permits the substrates to be made thin because it forms the microcap in situ and avoids the handling of the fragile microcap during assembly.

A description of additional details regarding embodiments of methods of assembling a lid substrate to a base substrate is provided in U.S. Pat. No. 6,425,911, which description is hereby incorporated herein by reference as if set forth herein.

When the base substrate and lid substrate are bonded together as described above a hermetically-sealed volume is formed between the lid substrate and the base substrate. In that case, the acoustic resonator, the low-resistivity material layer (e.g., epitaxial layer) region, the electronic circuitry, the second bonding pad(s), and the drop down contact post(s) are disposed within the hermetically-sealed volume.

In some embodiments, base substrates **410/510**, and lid substrates **420/520**, are individually parametrically tested prior to bonding the semiconductor substrates together.

The packaging arrangement illustrated above with respect to packaged FMOS devices **400** and **500** may be employed for a variety of electronic devices.

In some embodiments, packaged FMOS devices **400** and/or **500** may comprise an oscillator, mixer and other possible electronic circuits. In that case, electronic circuitry **426/526** may comprise oscillator circuitry that includes one or more transistors or other active devices of the oscillator. Beneficially, the packaging arrangement of packaged FMOS

devices **400** and **500** may provide certain benefits for such an oscillator, including a small size, and tight coupling between the resonator and the active circuitry of the oscillator which can reduce noise and losses and therefore improve performance of the oscillator.

FIG. **7** shows an example embodiment of a packaged FMOS device **700** with two FBAR oscillators that may be employed in a combined accelerometer and rotation detector.

Packaged FMOS device **700** comprises a base substrate **710** and a lid substrate **720**.

Base substrate **710** has on a first surface (top surface as shown in FIG. **7**) thereof: first bonding pads **711a**, **711b** and **711c**; a second bonding pad **713**; first recessed regions **714a** and **714b**; and a second recessed region **716**. Base substrate **710** further includes on the first surface thereof a peripheral pad not shown in FIG. **7**, but examples of which are illustrated in FIGS. **5** and **6A** above. Beneficially, first bonding pads **711** and second bonding pad(s) **713**, and the peripheral pad are formed of an electrically conductive (e.g., metal) material. Also, in some embodiments base substrate **710** may include additional first and second bonding pads **711** and **713**.

Lid substrate **720** has on a first surface (bottom surface as shown in FIG. **7**) thereof: bonding pad seals **721a**, **721b** and **721c**, each having a corresponding through hole **722a**, **722b** and **722c** formed in lid substrate **720**; a drop down contact post **723**; a pedestal **724**; a low-resistivity material layer region **725**; and electronic circuitry **726** formed on low-resistivity material layer region **725**. Lid substrate **720** further includes on the first surface thereof a peripheral pad seal not shown in FIG. **7**, but examples of which are illustrated in FIGS. **5** and **6B**. Beneficially, bonding pad seals **721a**, **721b** and **721c** and drop down contact post **723** each have an electrically conductive (e.g., a metal such as gold) layer thereon for making contact with the corresponding bonding pads **711** and **713**. Also, in some embodiments lid substrate **720** may include additional bonding pad seals **721** and/or additional drop down contact posts **723**. In some embodiments, one or more of through holes **722** in lid substrate **720** are plated or otherwise filled with a conductive material (e.g., metal) to provide an electrical connection between the metal layer of a corresponding bonding pad seal **721** and a second surface (top surface as shown in FIG. **7**) of lid substrate **720**, for example a pad on the second surface of lid substrate **720**. As shown in FIG. **7**, in some embodiments, bonding pad seals **721** and/or drop down contact posts **723** include treads or gaskets that are covered with the electrically conductive material.

Packaged FMOS device **700** further comprises acoustic resonators **717a** and **717b** disposed on base substrate **710** above corresponding first recessed regions **714a** and **714b**. In some embodiments, acoustic resonators **717a** and **717b** are each electrically connected to electronic circuitry **726**, for example by means of first and/or second bonding pads **711**, **713** and the conductive (e.g., metal) layer on bonding pad seal(s) **721** and/or drop down contact post **723**. In some embodiments, each of the acoustic resonators **717a** and **717b** comprises a film bulk acoustic resonator (FBAR). In other embodiments, a solidly mounted resonator (SMR) may be employed. In some embodiments, electronic circuitry **726** includes one or more transistors or other active devices for two oscillators (e.g., oscillators **310** and **320** of FIG. **3**) that operate respectively with acoustic resonators **717a** and **717b**. In some embodiments, electronic circuitry **726** may include one or more other elements shown in FIG. **3**, including for example first mixer **330**, diplexer **340**, second mixer **360** and/or filter **370**.

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In some embodiments, base substrate **710** and/or lid substrate **720** comprise a semiconductor substrate. In some embodiments, lid substrate **720** can be made of an electronically non-conductive material or a high-resistivity semiconductor material, such as single crystal silicon. Also, in some

embodiments when lid substrate **720** is a semiconductor substrate, low-resistivity material layer region **725** comprises an epitaxial layer formed on the semiconductor substrate. In alternative embodiments, lid substrate **720** may comprise other high-resistivity materials, for example a silicon-on-insulator (SOI) substrate, and low-resistivity material layer region **725** may be formed by controlled doping of the SOI substrate.

In some embodiments, base substrate **710** and lid substrate **720** are made of materials that have the same or approximately the same coefficient of thermal expansion (CTE) as each other to avoid thermal expansion mismatch problems. In some embodiments base substrate **710** and lid substrate **720** are made of the same semiconductor material as each other.

As noted above, in some embodiments lid substrate **720** is a semiconductor substrate. In general, such a semiconductor substrate on which electronic circuitry **726** is to be fabricated will have a low-resistivity material layer disposed on all or substantially all of a surface thereof for the formation of the semiconductor or active devices of electronic circuitry **726**. In particular, such a low-resistivity material layer comprises a material that has a substantially lower resistivity than the high-resistivity semiconductor material of lid substrate **720**. As used herein, “substantially lower resistivity” means about one order of magnitude lower resistivity, or more than one order of magnitude lower resistivity, for example as measured in terms of Ω -cm. For example, in some embodiments, the high-resistivity semiconductor material of lid substrate **720** has a resistivity of more than 1000 Ω -cm, while the low-resistivity material of a low-resistivity material layer has a resistivity of less than 100 Ω -cm, including in some embodiments a resistivity in a range of 10 Ω -cm. Accordingly, if left intact on lid substrate **720**, such a low-resistivity material layer may provide a low impedance path or electrical short between the conductive (e.g., metal) layer(s) of bonding pad seals **721** and/or drop down contact post(s) **723**. This can degrade the performance of packaged FMOS device **700**, and in some cases may render packaged FMOS device **700** inoperable.

Accordingly, in some embodiments one or more portions of the low-resistivity material layer is removed between bonding pad seals **721**, drop down contact posts **723**, and the peripheral pad seal so as to eliminate a current path through the low-resistivity material layer between any of the bonding pad seals **721**, drop down contact posts **723**, and the peripheral pad seal. Furthermore, in some embodiments one or more portions of the low-resistivity material layer are removed so as to eliminate a current path between low-resistivity material layer region **725** and the conductive layer(s) of some or all of the bonding pad seals **721**, and/or drop down contact posts **723**, and/or the peripheral pad seal.

In a particular embodiment of packaged FMOS device **700** shown in FIG. 7, the low-resistivity material layer (e.g., epitaxial layer) is eliminated except for: (1) low-resistivity material layer (e.g., epitaxial layer) region **725**, which is isolated from some or all of the bonding pad seals **721**, and/or drop down contact posts **723**, and/or the peripheral pad seal; and (2) one or more low-resistivity material layer (e.g., epitaxial layer) portions remaining in the treads of one or more of the bonding pad seal(s) **721**, drop down contact post(s) **723**, and the peripheral pad seal. Furthermore, lid substrate **720** of packaged FMOS device **700** includes an electrically insulat-

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ing material **727** (e.g., an oxide such as silicon oxide) electrically isolating low-resistivity material layer (e.g., epitaxial layer) region **725** from one or more electrically conductive (e.g., metal) layers or traces in contact with bonding pad seal(s) **721** and drop down contact post(s) **723**. In some embodiments, electrically insulating material **727** partially or totally encompasses or surrounds low-resistivity material layer (e.g., epitaxial layer) region **725**.

In some embodiments, lid substrate **720** may have a low-resistivity material layer (e.g., epitaxial layer) formed entirely on the first surface thereof, and the low-resistivity material layer (e.g., epitaxial layer)—except for low-resistivity material layer (e.g., epitaxial layer) region **725** and the low-resistivity material layer (e.g., epitaxial layer) portions remaining in the treads—may be removed after formation of electronic circuitry **726**. In other embodiments, the low-resistivity material layer (e.g., epitaxial layer)—except for low-resistivity material layer (e.g., epitaxial layer) region **725** and the low-resistivity material layer (e.g., epitaxial layer) portions remaining in the treads—may be removed before formation of electronic circuitry **726**.

In other embodiments, the low-resistivity material layer (e.g., epitaxial layer) is only removed in areas surrounding each of the bonding pad seals **721**, and/or drop down contact posts **723**, and/or the peripheral pad seal so as to electrically isolate the bonding pad seals **721**, and/or drop down contact posts **723**, and/or the peripheral pad seal from each other and/or from electronic circuitry **726**.

While example embodiments are disclosed herein, one of ordinary skill in the art appreciates that many variations that are in accordance with the present teachings are possible. The invention therefore is not to be restricted except within the scope of the claims.

The invention claimed is:

1. A device, comprising:

a base substrate having a first bonding pad and a peripheral pad provided thereon, the peripheral pad encompassing the first bonding pad;

a first acoustic resonator and a second acoustic resonator disposed on the base substrate;

a lid substrate having a bonding pad seal and a peripheral pad seal provided thereon, the bonding pad seal bonding around the perimeter of the first bonding pad and the peripheral pad seal bonding with the peripheral pad to define a hermetically sealed volume between the lid substrate and the base substrate, the lid substrate defining a through hole therein positioned over the first bonding pad, the through hole providing access for an electrical connection to the first bonding pad; and

electronic circuitry provided on a portion of a first surface of the lid substrate within the hermetically sealed volume, the electronic circuitry comprising:

first oscillator circuitry electrically connected with the first acoustic resonator to form a first oscillator, the first oscillator further being electrically connected to a first capacitor of a teeter-totter capacitive transducer such that a first oscillator frequency of the first oscillator changes in response to a change in the capacitance of the first capacitor; and

second oscillator circuitry electrically connected with the second acoustic resonator to form a second oscillator, the second oscillator further being electrically connected to a second capacitor of the teeter-totter capacitive transducer such that a second oscillator frequency of the second oscillator changes in response to a change in the capacitance of the second capacitor.

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2. The device of claim 1, wherein the electronic circuitry further comprises:

a mixer having first and second mixer inputs connected respectively to an output of the first oscillator and to an output of the second oscillator; and

a diplexer having an input connected to an output of the mixer and having first and second diplexer outputs, wherein the first diplexer output is configured to provide a first signal having a first frequency that is a function of one of: (1) an acceleration force applied to the teeter-totter capacitive transducer, and (2) a rotational force applied to the teeter-totter capacitive transducer.

3. The device of claim 2, wherein the first diplexer output is configured to provide the first signal having the first frequency that is a function of the rotational force, and the second diplexer output is configured to provide a second signal having a second frequency that is a function of the acceleration force.

4. The device of claim 3, further comprising:

a third oscillator;

a second mixer, having a first input connected to an output of the third oscillator, a second input connected to the second diplexer output, and an output; and

a low pass filter having an input connected to the output of the second mixer and being configured to output a third signal having a third frequency that is a function of the rotational force.

5. The device of claim 4, wherein the third oscillator includes a third acoustic resonator.

6. The device of claim 4, wherein in the absence of the acceleration force and the rotational force, the first oscillator frequency of the first oscillator and the second oscillator frequency of the second oscillator are substantially the same as each other, and wherein a third oscillator frequency of the third oscillator is substantially twice the first frequency.

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7. The device of claim 1, wherein in response to the acceleration force, the first oscillator frequency of the first oscillator is increased and the second oscillator frequency of the second oscillator is also increased.

8. The device of claim 1, wherein in response to the rotational force, the first oscillator frequency of the first oscillator is decreased and the second oscillator frequency of the second oscillator is increased.

9. The device of claim 1, further comprising a die including the teeter-totter capacitive transducer.

10. The device of claim 1, wherein the first acoustic resonator, or the second acoustic resonator, or both, are a film bulk acoustic resonator (FBAR).

11. The device of claim 1, wherein the first acoustic resonator, or the second acoustic resonator, or both, are a solidly mounted resonator (SMR).

12. The device of claim 1, wherein the first acoustic resonator, or the second acoustic resonator, or both, are a zero drift resonator (ZDR).

13. The device of claim 1, wherein the lid substrate comprises a comparatively low-resistivity material layer region.

14. The device of claim 13, wherein the electronic circuitry is disposed over the comparatively low-resistivity material layer region.

15. The device of claim 13, wherein the comparatively low-resistivity material layer region comprise.

16. The device of claim 1, wherein an electrically conductive layer is disposed over the bonding pad seal.

17. The device of claim 1, further comprising a drop down contact post.

18. The device of claim 17, wherein an electrically conductive layer is disposed over the drop down post.

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